QE and Emittance from Free Electron Metals

Photocathode Physics for Photoinjectors 2012

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Background for Bi-Alkali Antimonide Research

NGLS: 2.5 GeV CW SC Linac producing ultrafast coherent X-rays High brightness (≤ 1 mm-mrad, ≤ 1 nC) High rep rate (MHz), synchronized with photocathode



- Cu fast, relatively robust, 5e-5 QE in UV 1 nC @ 1 MHz reprate -> ~ KW of IR
- GaAs:Cs:O slow depending on λ , hyper-reactive, 10% QE in visible 1 nC @ 1 MHz reprate -> ~ mW of IR
- Cs₂Te fast, relatively robust at ~ 10^{-9} Torr, 10% QE in UV 1 nC @ 1 MHz reprate -> ~ W IR
- K_2 CsSb fast, somewhat reactive at 10⁻⁹ Torr, 1% QE in visible 1 nC @ 1 MHz reprate -> ~ mW of IR

Choice made to study K_2CsSb based on work by D. Dowell et al., NIM 356 2-3, 167 1995

Initial QE Measurements on K₂CsSb

Basic Recipe (current):

- 1) HF Dipped Si substrate heat cleansed at 600° C
- 2) 200 Å Sb deposited at 160° C
- 3) K deposited at 140° C till max QE
- 4) Cs deposited at 120° C till max QE
- 5) 3 + 4 are repeated as needed



Different recipes produce similar results wrt QE High temp step + rapid cooling work but not necessary

Results:

- 1) Nominally 6% QE at 532
- 2) 100 μm focused green laser maintained current density of 1 mA/mm² for weeks w/o decay
- 3) 50% decay time of QE at 5e-9 torr pp H_2O around 17 h

Vecchione et al., APL 99, 034103 (2011)



Initial Transverse Emittance Measurements on K₂CsSb

Transverse momentum distribution for K_2CsSb measured at 543 nm Simple model: Dowell et al., NIM Phys. Res. A 622, 685 (2010)











Experimental Methods (Brief)



- Work Function: Biased -10V emission recorded w/ Keithley 6517B (noise ~ 10s fA) ~10 mm² collimated beam normal incident via fused quartz viewport Photon flux calibrations performed using AXUV photodiode
- Emittance: 900 V channel plate before beam accelerated 3.1 kV into phosphor Lens coupled CCD camera imaged using 0.1 - 10 s exposures Convergent light focused through grid at 30° into 0.1-0.2 mm spot *** Instrumental resolution estimated to be less than kT
- Sample Prep:HF Dipped polished Si substrate phosphor doped <100> $1x10^{-12} \Omega$ -cmFilms deposited using low temperature effusion or DC sputtering
Monitored using quartz monitor, base pressures ~ $1-2x10^{-10}$ torr

Best Guess* of Results from Oxidized Antimony



*Data slightly processed

Transverse Momentum Distributions - Oxidized Antimony



Disclaimer: Systematic fitting of > 1 million images is ongoing process Results presented today may change a bit before publication

Quantifying the Effects of Roughness?



RMS Emittance at 0.2 MV/m Extraction

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- 1) Preheat HF dipped substrate to 500 C
- 3) Sputter at room temperature or evaporate at ~ 160 C
- 4) Sample oxidized before taking data

0808: exposed to wet air and then re-heated to 125 °C 0817: exposed to oxygen and water via ambient vacuum

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Conclusions

- QE experiences a gradual onset of emission at work function Effect originates from finite temperature of cathode
 i.e. Fermi-Dirac distribution not modeled by step function
- 2) Emittances measured plateau at a finite value of ~ 0.23 μ m/mm Value conventionally referred to as "thermal emittance" Effect also originates from finite temperature of cathode
- 3) Predictions are close to measurements but inconsistencies remain Fitting may be complicated by non-flat density of states Averaging of crystallographic grains also needs consideration
- 4) Roughness effects are believed to have been observed At most ~ 20% increase in overall emittance Theory focused on including power-spectral density of surface
- 5) Efforts continue to refine experimental measurements Currently focused on making a wide range of samples May be time to reboot experiment to refine each measurement aspect
- 6) Questions are fundamentally important + interesting Hope is future experiments will increase our understanding!